Thermal Atomic Layer Etching of ZnO by "Conversion-Etch" Using Hydrogen Fluoride and Trimethylaluminum

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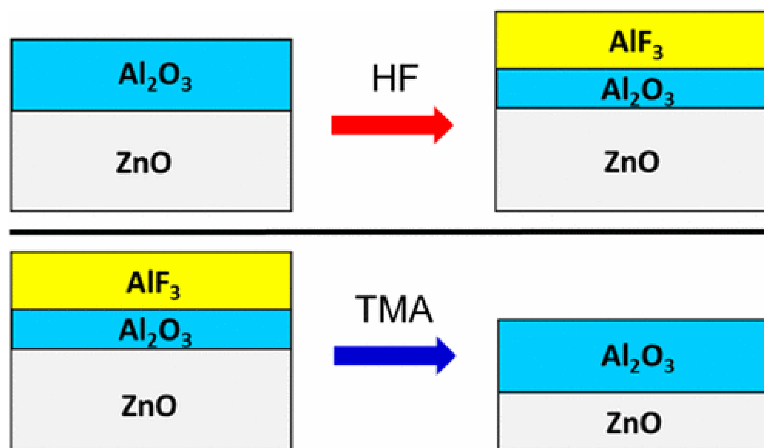

Figure 1. Schematic showing the surface layers resulting from the sequential HF and TMA exposures during ZnO ALE by "conversion-etch" at 265 °C.

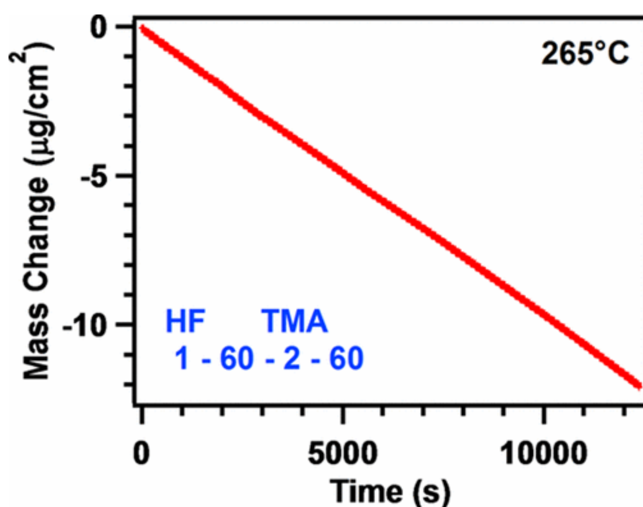

Figure 2. Mass change versus time for ZnO ALE using sequential exposures of HF and TMA at 265°C.

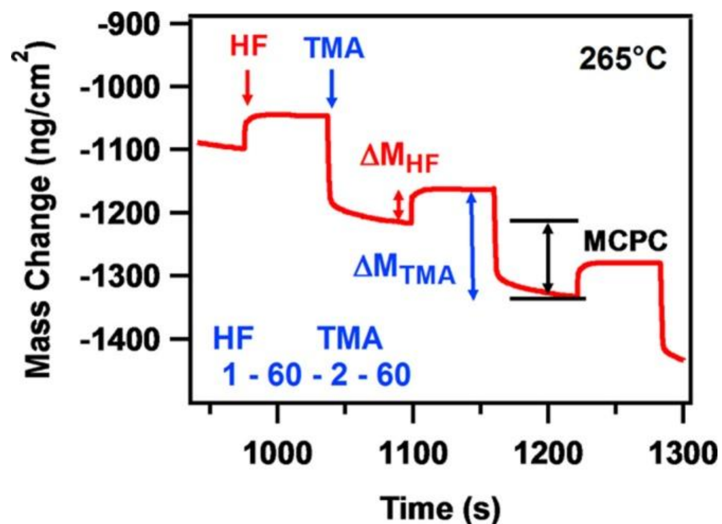

Figure 3. Expanded segment of Figure 2 showing mass changes during ZnO ALE using sequential exposures of HF and TMA at 265°C.